

2.5V Drive Pch+Pch MOSFET

US6J2

●Structure

Silicon P-channel MOSFET

●Features

- 1) Two Pch MOSFET transistors in a single TUMT6 package.
- 2) Mounting cost and area can be cut in half.
- 3) Low on-resistance.
- 4) Low voltage drive (2.5V) makes this device ideal for portable equipment.
- 5) Drive circuits can be simple.

●Applications

Switching

●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
US6J2		○

●Absolute maximum ratings (Ta=25°C)

<It is the same ratings for Tr1 and Tr2>

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	-20	V
Gate-source voltage	V _{GSS}	±12	V
Drain current	Continuous	I _D	±1 A
	Pulsed	I _{DP} *1	±4 A
Source current (Body diode)	Continuous	I _S	-0.4 A
	Pulsed	I _{SP} *1	-4 A
Total power dissipation	P _D *2	1.0	W / TOTAL
		0.7	W / ELEMENT
Channel temperature	T _{ch}	150	°C
Range of Storage temperature	T _{stg}	-55 to +150	°C

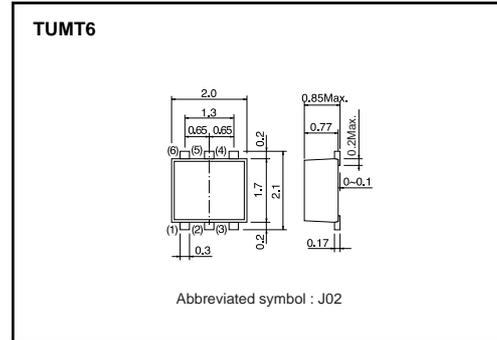
*1 Pw≤10μs, Duty cycle≤50%
 *2 Mounted on a ceramic board

●Thermal resistance

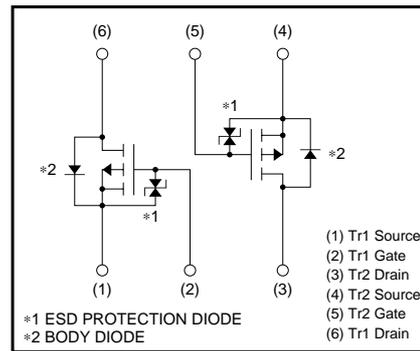
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) *	125	°C/W / TOTAL
		179	°C/W / ELEMENT

* Mounted on a ceramic board

●Dimensions (Unit : mm)



●Inner circuit



Transistors

●Electrical characteristics (Ta=25°C)

<It is the same characteristics for Tr1 and Tr2 MOSFET>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	±10	μA	V _{GS} =±12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	–20	–	–	V	I _D = –1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	–1.0	μA	V _{DS} = –20V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	–0.7	–	–2.0	V	V _{DS} = –10V, I _D = –1mA
Static drain-source on-state resistance	R _{DS(on)} *	–	280	390	mΩ	I _D = –1A, V _{GS} = –4.5V
		–	310	430	mΩ	I _D = –1A, V _{GS} = –4V
		–	570	800	mΩ	I _D = –0.5A, V _{GS} = –2.5V
Forward transfer admittance	Y _{fs} *	0.7	–	–	S	V _{DS} = –10V, I _D = –0.5A
Input capacitance	C _{iss}	–	150	–	pF	V _{DS} = –10V
Output capacitance	C _{oss}	–	20	–	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	–	20	–	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	–	9	–	ns	I _D = –0.5A
Rise time	t _r *	–	8	–	ns	V _{DD} ≐ –15V
Turn-off delay time	t _{d(off)} *	–	25	–	ns	V _{GS} = –4.5V
Fall time	t _f *	–	10	–	ns	R _L =30Ω
Total gate charge	Q _g *	–	2.1	–	nC	V _{DD} ≐ –15V R _L =15Ω
Gate-source charge	Q _{gs} *	–	0.5	–	nC	V _{GS} = –4.5V R _G =10Ω
Gate-drain charge	Q _{gd} *	–	0.5	–	nC	I _D = –1A

* Pulsed

<Body diode (Source-drain)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	–	–	–1.2	V	I _S = –0.4A, V _{GS} =0V

Transistors

●Electrical characteristic curves

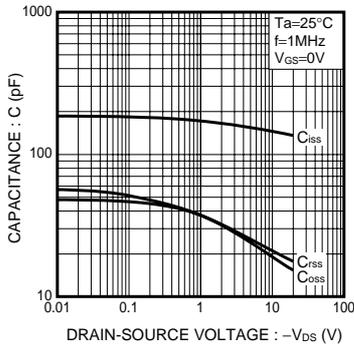


Fig.1 Typical Capacitance vs. Drain-Source Voltage

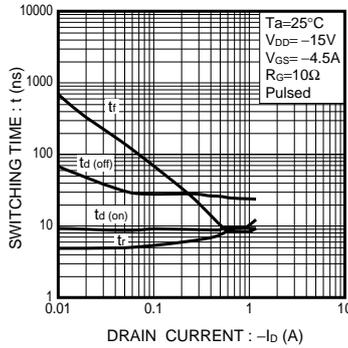


Fig.2 Switching Characteristics

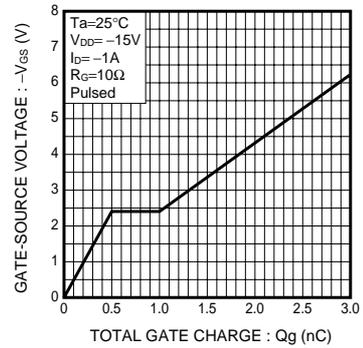


Fig.3 Dynamic Input Characteristics

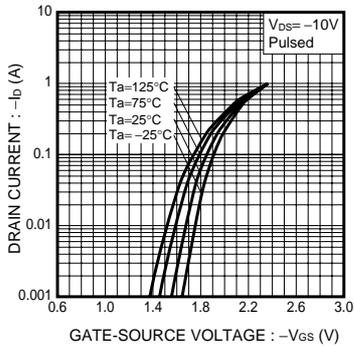


Fig.4 Typical Transfer Characteristics

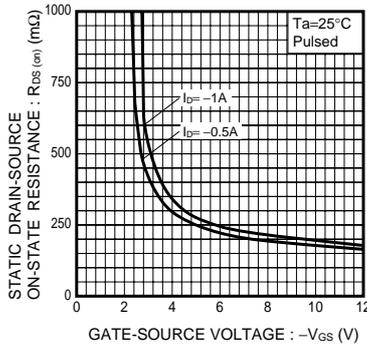


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

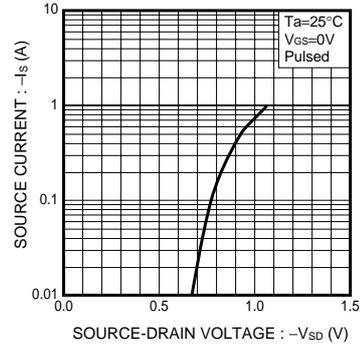


Fig.6 Source Current vs. Source-Drain Voltage

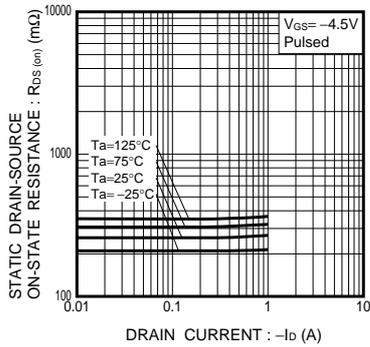


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (II)

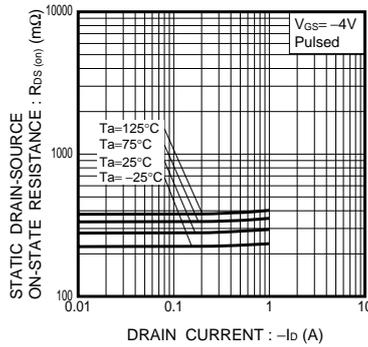


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (III)

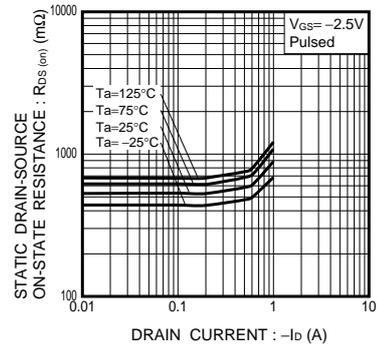


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (I)

Transistors

●Measurement circuits

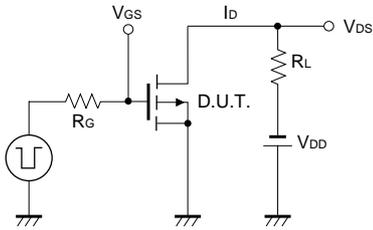


Fig.10 Switching Time Measurement Circuit

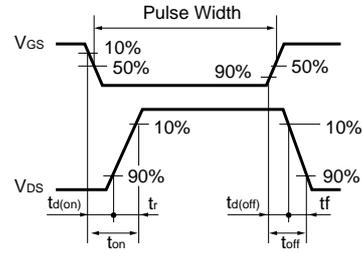


Fig.11 Switching Waveforms

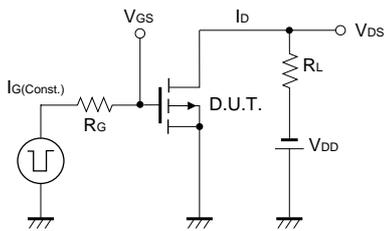


Fig.12 Gate Charge Measurement Circuit

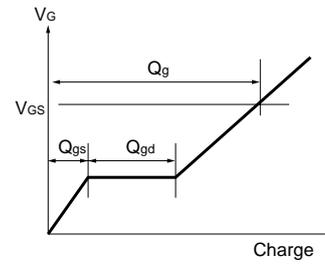


Fig.13 Gate Charge Waveform

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